

L Number	Hits	Search Text	DB	Time stamp
-	110	vacancy near2 dominat\$ and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 09:20
-	33	vacancy near2 dominat\$ and silicon and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:19
-	2	20020121238.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 09:22
-	1	0022197.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 09:25
-	58	"0022197"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 09:33
-	16	vacancy near2 dominat\$ near20 segment and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 09:37
-	21	idEAL near2 OXYGEN near2 PRECIPITATING near2 SILICON	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:08
-	1	vacancy near2 dominat\$ and void near2 density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:09
-	1660	void near2 density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:09
-	7	void near2 density and silicon adj ingot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:09
-	8	void near2 density and silicon near2 ingot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:11
-	1	void near2 density and memc.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:12
-	53	residual near5 vacancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:12
-	17	residual near5 vacancy and silicon near10 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 10:12

-	101	vacancy near2 dominat\$ and silicon near10 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:19
-	1	(vacancy near2 dominat\$ and silicon near10 (wafer or ingot)) and void near4 density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:19
-	39	(vacancy near2 dominat\$ and silicon near10 (wafer or ingot)) and void	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:20
-	41	(vacancy near2 dominat\$ and silicon near10 (wafer or ingot)) and nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:21
-	3	(vacancy near2 dominat\$ and silicon near10 (wafer or ingot)) and nitrogen near10 less	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:22
-	22	(vacancy near2 dominat\$ and silicon near10 (wafer or ingot)) and nitrogen near10 (content or concentration or amount)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:27
-	395	silicon near2 (wafer or ingot) and nitrogen near10 (content or concentration or amount) near10 less	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:28
-	34	silicon near2 (wafer or ingot) same nitrogen near5 (content or concentration or amount) near5 less	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:32
-	9	silicon near2 (wafer or ingot) same "13 ppma"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:33
-	157	vacancy same void and (si or silicon) near10 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 11:05
-	123	vacancy near10 void and (si or silicon) near10 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 11:06
-	34	vacancy near10 void near10 (density or content or concentration) and (si or silicon) near10 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 11:17
-	172	vacancy near10 agglomerat\$ and (silicon or si) near2 (ingot or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 11:17
-	90	vacancy near10 agglomerat\$ and (silicon or si) near2 (ingot or wafer) and vacancy near3 dominat\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 11:18

-	79	vacancy near10 agglomerat\$ same dominat\$ and (silicon or si) near2 (ingot or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:18
-	68	vacancy near10 agglomerat\$ near10 dominat\$ and (silicon or si) near2 (ingot or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:29
-	34	vacancy near3 agglomerat\$ near10 dominat\$ and (silicon or si) near2 (ingot or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:49
-	379748	low near5 oxygen near10 ppma same fault and (si or silicon) near3 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:50
-	27	low near5 oxygen near10 ppma same fault and (si or silicon) near3 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 12:00
-	53	residual near5 vacancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 12:00
-	19	residual near5 vacancy and (si or silicon) near4 (ingot or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 12:04
-	2	"2000183068"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 12:52
-	47	\$2control\$4 near10 precipitat\$ same vacancy and (si or silicon) near2 (ingot or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 12:59
-	71	"0014776"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:05
-	3	agglomerat\$ near3 vacancy near10 radius near10 nm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:12
-	5	agglomerat\$ near3 vacancy near10 nm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:12
-	83	agglomerat\$ near3 vacancy near15 (diameter or radius or width or size)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:13
-	79	agglomerat\$ near3 vacancy near10 (diameter or radius or width or size)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:35

-	49	agglomerat\$ near3 vacancy near10 integ\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 13:41
-	83	agglomerat\$ near3 vacancy near10 (size or density)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 13:53
-	32	agglomerat\$ near3 vacancy near10 size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 13:55
-	0	6146459.pn. and agglomer\$ near3 size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 13:56
-	2	6146459.pn. and agglomer\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 14:51
-	45	residual near4 vacancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 14:52

L Number	Hits	Search Text	DB	Time stamp
1	879	428/64.1.ccls.	USPAT; US-PGPUB	2004/03/05 15:15
2	0	428/64.1.ccls. and void adj density	USPAT; US-PGPUB	2004/03/05 15:15
3	118	428/64.1.ccls. and defects	USPAT; US-PGPUB	2004/03/05 15:15
4	890	428/64.4.ccls.	USPAT; US-PGPUB	2004/03/05 15:16
5	7	428/64.4.ccls. and silicon adj wafers	USPAT; US-PGPUB	2004/03/05 15:16
6	428	117/13.ccls.	USPAT; US-PGPUB	2004/03/05 15:16
7	190	117/13.ccls. and ingot	USPAT; US-PGPUB	2004/03/05 15:16
8	133	(117/13.ccls. and ingot) and defects	USPAT; US-PGPUB	2004/03/05 15:18
9	122	117/20.ccls.	USPAT; US-PGPUB	2004/03/05 15:18
10	554	117/932.ccls.	USPAT; US-PGPUB	2004/03/05 15:18
11	26	117/932.ccls. and voids	USPAT; US-PGPUB	2004/03/05 15:18
-	2	average adj void adj density	USPAT; US-PGPUB	2004/03/04 17:14
-	65	density same agglomerated adj defects	USPAT; US-PGPUB	2004/03/04 17:48
-	66	(void adj density) not (density same agglomerated adj defects)	USPAT; US-PGPUB	2004/03/04 17:19
-	68	density same agglomerated adj defects	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:23
-	38	density near agglomerated adj defects	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:23
-	0	(density near agglomerated adj defects) not (density same agglomerated adj defects)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:23
-	1929	density same agglomerated	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:25
-	0	"118" near defects	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:24
-	217	(density same agglomerated) and defects	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:26
-	68	density same agglomerated near defects	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:25
-	0	(density same agglomerated near defects) not (density same agglomerated adj defects)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:25

-	80	agglomerated adj defects	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:26
-	77	(agglomerated adj defects) and density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:26
-	9	((agglomerated adj defects) and density) not (density same agglomerated adj defects)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:27
-	67	void adj density	USPAT; US-PGPUB	2004/03/04 17:42
-	0	high adj denstiy same agglomerated adj defects	USPAT; US-PGPUB	2004/03/04 17:49
-	0	high adj denstiy same vacancy adj defects	USPAT; US-PGPUB	2004/03/04 17:49
-	0	high adj denstiy same vacancy	USPAT; US-PGPUB	2004/03/04 17:49
-	628	void adj size	USPAT; US-PGPUB	2004/03/05 10:59
-	1	void adj size near radius	USPAT; US-PGPUB	2004/03/05 10:59
-	31	void adj radius	USPAT; US-PGPUB	2004/03/05 11:00
-	1	(void adj size) and agglomerated adj defects	USPAT; US-PGPUB	2004/03/05 11:00
-	7	(void adj size) and defects and vacancy	USPAT; US-PGPUB	2004/03/05 11:12
-	994	defect adj size	USPAT; US-PGPUB	2004/03/05 11:23
-	1218	small adj voids	USPAT; US-PGPUB	2004/03/05 13:11
-	40	(small adj voids) and silicon adj wafer	USPAT; US-PGPUB	2004/03/05 15:15
-	5	((small adj voids) and silicon adj wafer) and void near size	USPAT; US-PGPUB	2004/03/05 13:15